



AL8812

BOOST/BUCK DC-DC CONVERTER FOR DIMMABLE MR16 LED LAMPS

Description

The AL8812 is a monolithic control circuit containing the primary functions required for DC-to-DC converters with MOSFET in one package. These devices consist of an internal temperature compensated reference, comparator, controlled duty cycle oscillator with an active current limit circuit, driver and high current output switch. Additionally a 60V, 3.6A MOSFET is integrated for reduced BOM cost and size. This series is specifically designed for buck and boost applications with a minimum number of external components.

Pin Assignments

Applications

Low Voltage LED Lighting such as MR-16

General Purpose DC-DC Converter



Features

- Operation from 3.0V to 20V Input
- Integrated 60V, 3.6A MOSFET
- Low Standby Current
- Current Limiting
- Output Voltage Adjustable
- Frequency Operation to 100 kHz
- Precision 2% Reference
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Notes:

es: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Typical Applications Circuit



Dimmable MR-16 LED Driver System Diagram

(For detailed schematic please contact your Diodes Sales Representative)



AL8812

Pin Descriptions

Pin Name	Pin Number (U-DFN6040-12)	Function
NC	1	No Connection
GATE	2	Gate connection of internal MOSFET.
INPUT	3	Feedback pin for inverting input of internal comparator
VCC	4	Supply voltage pin
SENSE	5	No Connection.
DRIVE	6	Current drive collector:
DRIVE	0	Normally connected to V_{CC} directly or via a resistor.
SW/C	7	Internal switch transistor collector
SW/E	8	Internal switch transistor emitter
GND	9	Ground Connection
TIMING	10	Timing Capacitor to control the switching frequency.
SOURCE	11	Source connecton of internal MOSFET
DRAIN	12	Drain connection of internal MOSFET
Exposed PAD1		Exposed Pad of MOSFET Drain
Exposed PAD2		Exposed Pad of AL8812 and connect to PCB ground

Functional Diagram





Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Symbol	Parameter	Value	Unit	
V _{CC}	Power Supply Voltage	20	V	
V _{IR}	Comparator Input Voltage Range	-0.3 to +36	V	
SW/C	Switch Collector Voltage	36	V	
SW/E	Switch Emitter Voltage (V _{Pin} 1 = 40V)	36	V	
V _{CE (switch)}	Switch Collector to Emitter Voltage	36	V	
DRIVE	Driver Collector Voltage	36	V	
I _{C (driver)}	Driver Collector Current (Note 4)	100	mA	
Isw	Switch Current	1.6	А	
V _{DS}	Maximum MOSFET Drain-Source voltage	60	V	
V _{GS}	Maximum MOSFET Gate-Source voltage	+/-20	V	
ISOURCE	Maximum Continuous Source (Body Diode) Current	3.7	А	
PD	Continuous Power Dissipation (T _A = +25°C) (U-DFN6040-12 (derate 10mW/°C above +25°C)	1000	mW	
θ _{JA}	Junction-to-Ambient Thermal Resistance	47.31	°C/W	
θ」С	Junction-to-Case Thermal Resistance	6.42	°C/W	
T _{MJ}	Maximum Junction Temperature	+150	°C	
T _{OP}	Operating Junction Temperature Range	0 to +105	°C	
T _{stg}	Storage Temperature Range	-65 to +150	°C	
ESD HBM	Human Body Model ESD Protection	250	V	
ESD MM	Machine Model ESD Protection	100	V	

Note: 4. Maximum package power dissipation limits must be observed.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Symbol	Characteristics	Min	Тур	Max	Unit	
OSCILLATOR						
f _{osc}	Frequency (V _{PIN} 5 = 0V, C_T = 1.0nF, T_A = +25°C)	24	33	42	kHz	
I _{chg}	Charge Current (V _{CC} = 5.0V to 40V, T _A = +25°C)	24	30	42	μA	
I _{dischg}	Discharge Current (V _{CC} = 5.0V to 40V, T_A = +25°C)	140	200	260	μA	
I _{dischg} / I _{chg}	Discharge to Charge Current Ratio (Pin 7 to V_{CC} , $T_A = +25^{\circ}C$)	5.2	6.5	7.5	—	
Vipk (sense)	Current Limit Sense Voltage ($I_{chg} = I_{dischg}, T_A = +25^{\circ}C$)	300	400	450	mV	
OUTPUT SWITC	CH (Note 5)					
V _{CE (sat)}	Saturation Voltage, Darlington Connection (I _{SW} = 1.0A, Pins 1,8 connected)	_	1.0	1.3	V	
V _{CE (sat)}	Saturation Voltage, Darlington Connection (I_{SW} = 1.0A, ID = 50mA, Forced $\beta \approx 20$)	_	0.45	0.7	V	
h _{FE}	DC Current Gain (I_{SW} = 1.0A, V_{CE} = 5.0V, T_A = +25°C)	50	75	_	_	
I _{C (off)}	Collector Off-State Current (V _{CE} = 40V)	-	0.01	100	μA	
OUTPUT MOSF	ET					
V _{GS(th)}	MOSFET Gate Threshold voltage	1	_	2.2	V	
V _{FD}	MOSFET Diodes forward voltage	_	.85	.95	V	
R _{DS(ON)}	Drain-source on-resistance (VGS = 10V, ID = 2.5A) Drain-source on-resistance (VGS = 4.5V, ID = 2A)	_	_	120 180	mΩ mΩ	
COMPARATOR						
V _{th}	Threshold Voltage		_	_	V	
_	T _A = +25°C		1.25	1.275	_	
	$T_A = 0^{\circ}C \text{ to } +70^{\circ}C$		_	1.29	—	
Reg _{line}	Threshold Voltage Line Regulation (V _{CC} = 3.0V to 40V)	_	1.4	6.0	mV	
TOTAL DEVICE						
Icc	Supply Current (V _{CC} = 5.0V to 40V, C _T =1.0nF, Pin 7 = V _{CC} , V _{Pin 5} > V _{th} Pin 2 = Gnd, remaining pins open)	_	—	3.5	mA	

Note: 5. Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient temperature as possible.



Performance Characteristics



Figure 3. Current Limit Sense Voltage versus Temperature







Figure 2. Reference Voltage versus Temp.



Figure 4. Standby Supply Current versus Supply Voltage











Typical Application Circuits

Circuits shown below represent connections employed for different topologies. To use the integrated MOSFET the typical configuration below can be used.





Typical Application Circuits (cont.)

Boost Converter



Test	Conditions	Results	
Line Regulation	V_{in} = 9V to 12V, I_O = 200mA	20mV = ±0.035%	
Load Regulation	V_{in} = 12V, I_O = 50mA to 200mA	15mV = ±0.035%	
Output Ripple	V _{in} = 12V, I _O = 200mA	500mV _{PP}	
Efficiency	V _{in} = 12V, I _O = 200mA	80%	

AL8812



AL8812

Typical Application Circuits (cont.)

Buck Converter



Test	Conditions	Results	
Line Regulation	V_{in} = 12V to 24V, I _O = 500mA	20mV = ±0.2%	
Load Regulation	V_{in} = 24V, I_O = 50mA to 500mA	5mV = ±0.05%	
Output Ripple	V _{in} = 24V, I _O = 500mA	160mV _{PP}	
Efficiency	V _{in} = 24V, I _O = 500mA	82%	



Design Formula Table

Calculation		Boost		Buck		
t / t	`	V _{OUT} + V _F -V _{IN (m}	iin)	V _{OUT} + v _F		
t _{ON} / t _{off}		V _{IN (min)} - V _{sat}		VIN (min) - VSAT - VOUT		
(t _{ON} + t _{off})		1/f		1/f		
		t _{ON} + t _{OFF}		t _{ON} + t _{OFF}		
t _{off}	to	ON	±1	t _{ON}	+1	
	toff +1		t _{OFF}	- + 1		
ton		(ton +toff) - tor	F	(ton +toff) - toff		
CT		4.0×10 ⁻⁵ t _{ON}		4.0×10		
I _{pk} (switch)	2l ₀	OUT (max) (t _{ON} / t _{off}	+1)	2I _{OUT (max)}		
R _{sc}		0.3 / Ipk (switch)		0.3 / Ipk (switch)		
	(VIN	(V _{IN (min)} – V _{sat}) Ipk (switch)		$t_{on (max)} = \frac{(V_{IN (min)} - V_{SAT} - V_{OUT})}{I_{pk (switch)}} ON$		
L (min)						
C.	9	I _{OUT} to	N	I _{pk (switch)} (t	OFF + t _{ON})	
Co	9	V _{ripple (pp)}		8V _{ripple (pp)}		

V_{sat} = Saturation voltage of the output switch.

V_F = Forward voltage drop of the output rectifier.

The following power supply characteristics must be chosen:

V_{IN} - Nominal input voltage.

 V_{OUT} - Desired output voltage, $|V_{OUT}|$ = 1.25 (1+R2/R1)

I_{OUT} - Desired output current.

 f_{min} - Minimum desired output switching frequency at the selected values of V_{in} and I_o.

Vripple(pp) - Desired peak-to-peak output ripple voltage. In practice, the calculated capacitor value will need to be increased due to its equivalent series resistance and board layout. The ripple voltage should be kept to a low value since it will directly affect the line and load regulation.



Ordering Information



			Tube		13" Tape and Reel	
Part Number	Package Code	Packaging	Quantity	Part Number Suffix	Quantity	Part Number Suffix
AL8812FDF-13	FDF	U-DFN6040-12	NA	NA	3000/Tape & Reel	-13

Marking Information

(1) U-DFN6040-12



Package Outline Dimensions (All dimensions in mm.)

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.





AL8812

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.500
G	0.650
G1	0.350
Х	0.250
X1	1.075
X2	1.275
X3	2.750
Y	0.400
Y1	1.150
Y2	1.000
Y3	2.300

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